

## MEDIUM-VOLTAGE DUAL BIDIRECTIONAL THYRISTOR OVERVOLTAGE PROTECTORS

## TISP31xxF3 (MV) Overvoltage Protector Series

Ion-Implanted Breakdown Region Precise and Stable Voltage Low Voltage Overshoot under Surge

DEVICE	V <sub>DRM</sub> V	V <sub>(BO)</sub> V
'3125F3	100	125
'3150F3	120	150
'3180F3	145	180

**Planar Passivated Junctions** Low Off-State Current <10 μA

#### **Rated for International Surge Wave Shapes**

Waveshape	Standard	I <sub>TSP</sub> A
2/10 μs	GR-1089-CORE	175
8/20 μs	IEC 61000-4-5	120
10/160 μs	FCC Part 68	60
10/700 μs	ITU-T K.20/21	50
10/700 μs	FCC Part 68	30
10/560 μs	FCC Part 68	45
10/1000 μs	GR-1089-CORE	35



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#### Description

These medium-voltage dual bidirectional thyristor protectors are designed to protect ground backed ringing central office, access and customer premise equipment against overvoltages caused by lightning and a.c. power disturbances. Offered in three voltage variants to meet battery and protection requirements, they are guaranteed to suppress and withstand the listed international lightning surges in both polarities. Overvoltages are initially clipped by breakdown clamping until the voltage rises to the breakover level, which causes the device to switch. The high crowbar holding current prevents d.c. latchup as the current subsides.

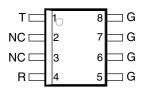
These monolithic protection devices are fabricated in ion-implanted planar structures to ensure precise and matched breakover control and are virtually transparent to the system in normal operation.

#### **How To Order**

Device	Package	Carrier	Order As
	D, Small-outline	Tape And Reeled	TISP31xxF3DR
TISP31xxF3	P, Plastic Dip	Tube	TISP31xxF3P
	SL, Single-in-line	Tube	TISP31xxF3SL

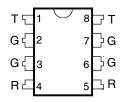
Insert 1xx value corresponding to protection voltages of 125, 150 and 180

#### D Package (Top View)



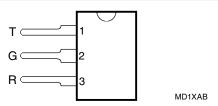
NC - No internal connection

#### P Package (Top View)

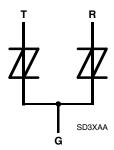


Specified T terminal ratings require connection of pins 1 and 8. Specified R terminal ratings require connection of pins 4 and 5.

#### SL Package (Top View)



#### **Device Symbol**



Terminals T, R and G correspond to the alternative line designators of A, B and C

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## Absolute Maximum Ratings, $T_A = 25$ °C (Unless Otherwise Noted)

Rating	Symbol	Value	Unit
Repetitive peak off-state voltage, 0 °C < T <sub>A</sub> < 70 °C '3125F3 '3150F3 '3180F3	$V_{DRM}$	±100 ±120 ±145	V
Non-repetitive peak on-state pulse current (see Notes 1 and 2)  1/2 (Gas tube differential transient, 1/2 voltage wave shape)		350	
2/10 (Telcordia GR-1089-CORE, 2/10 voltage wave shape) 1/20 (ITU-T K.22, 1.2/50 voltage wave shape, 25 $\Omega$ resistor)		175 90	
8/20 (IEC 61000-4-5, combination wave generator, 1.2/50 voltage wave shape) 10/160 (FCC Part 68, 10/160 voltage wave shape)	I <sub>PPSM</sub>	120 60	
4/250 (ITU-T K.20/21, 10/700 voltage wave shape, simultaneous) 0.2/310 (CNET I 31-24, 0.5/700 voltage wave shape)		55 38	A
5/310 (ITU-T K.20/21, 10/700 voltage wave shape, single) 5/320 (FCC Part 68, 9/720 voltage wave shape, single)		50 50	
10/560 (FCC Part 68, 10/560 voltage wave shape) 10/1000 (Telcordia GR-1089-CORE, 10/1000 voltage wave shape)		45 35	
Non-repetitive peak on-state current, 0 $^{\circ}$ C < T <sub>A</sub> < 70 $^{\circ}$ C (see Notes 1 and 3) 50 Hz, 1 s D Package		4.3	
P Package SL Package	I <sub>TSM</sub>	5.7 7.1	Α
Initial rate of rise of on-state current, Linear current ramp, Maximum ramp value < 38 A	di <sub>T</sub> /dt	250	A/μs
Junction temperature	T <sub>J</sub>	-65 to +150	°C
Storage temperature range	T <sub>stg</sub>	-65 to +150	°C

- NOTES: 1. Further details on surge wave shapes are contained in the Applications Information section.
  - 2. Initially, the TISP® must be in thermal equilibrium with 0 °C < T<sub>J</sub> <70 °C. The surge may be repeated after the TISP® returns to its initial conditions.
  - 3. Above 70 °C, derate linearly to zero at 150 °C lead temperature.

## Electrical Characteristics for R and T Terminal Pair, $T_A$ = 25 °C (Unless Otherwise Noted)

	Parameter Test Conditions		Min	Тур	Max	Unit
I <sub>DRM</sub>	Repetitive peak off- state current	$V_D = \pm 2V_{DRM}, 0  ^{\circ}C < T_A < 70  ^{\circ}C$			±10	μΑ
I <sub>D</sub>	Off-state current	$V_D = \pm 50 \text{ V}$			±10	μΑ
C <sub>off</sub>	Off-state capacitance		ge	0.05 0.065 0.03	0.15 0.2 0.1	pF

- NOTES: 4. These capacitance measurements employ a three terminal capacitance bridge incorporating a guard circuit. The third terminal is connected to the guard terminal of the bridge.
  - 5. Further details on capacitance are given in the Applications Information section.

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## Electrical Characteristics for T and G or R and G Terminals, $T_A$ = 25 $^{\circ}C$ (Unless Otherwise Noted)

	Parameter	Test Conditions		Min	Тур	Max	Unit
I <sub>DRM</sub>	Repetitive peak off- state current	$V_D = \pm V_{DRM}$ , 0 °C < $T_A$ < 70 °C				±10	μΑ
V <sub>(BO)</sub>	Breakover voltage	dv/dt = $\pm 250$ V/ms, R <sub>SOURCE</sub> = 300 $\Omega$	'3125F3 '3150F3 '3180F3			±125 ±150 ±180	V
V <sub>(BO)</sub>	Impulse breakover voltage	dv/dt $\leq$ ±1000 V/μs, Linear voltage ramp, Maximum ramp value = ±500 V R <sub>SOURCE</sub> = 50 Ω	'3125F3 '3150F3 '3180F3		±139 ±164 ±194		٧
I <sub>(BO)</sub>	Breakover current	$dv/dt = \pm 250 \text{ V/ms},  R_{SOURCE} = 300 \Omega$		±0.1		±0.6	Α
V <sub>T</sub>	On-state voltage	$I_T = \pm 5 \text{ A}, t_W = 100 \mu s$				±3	V
Ι <sub>Η</sub>	Holding current	$I_T = \pm 5 \text{ A, di/dt} = -/+30 \text{ mA/ms}$		±0.15			Α
dv/dt	Critical rate of rise of off-state voltage	Linear voltage ramp, Maximum ramp value < 0.85V <sub>DRM</sub>		±5			kV/μs
I <sub>D</sub>	Off-state current	$V_D = \pm 50 \text{ V}$				±10	μΑ
C <sub>off</sub>	Off-state capacitance				55 31 15	95 50 25	pF

NOTES: 6. These capacitance measurements employ a three terminal capacitance bridge incorporating a guard circuit. The third terminal is connected to the guard terminal of the bridge.

#### **Thermal Characteristics**

	Parameter	Test Conditions		Min	Тур	Max	Unit
		D -08W T -25°C	D Package			160	
$R_{\theta JA}$	Junction to free air thermal resistance	$P_{tot} = 0.8 \text{ W}, T_A = 25 ^{\circ}\text{C}$ 5 cm <sup>2</sup> . FR4 PCB	P Package			100	°C/W
		S CIII , I THA I OB	SL Package			135	

<sup>7.</sup> Further details on capacitance are given in the Applications Information section.

#### **Parameter Measurement Information**

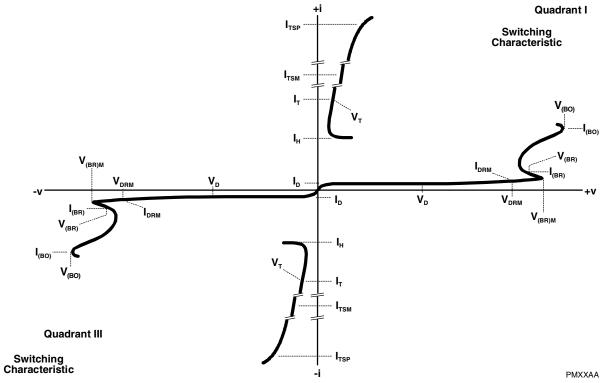
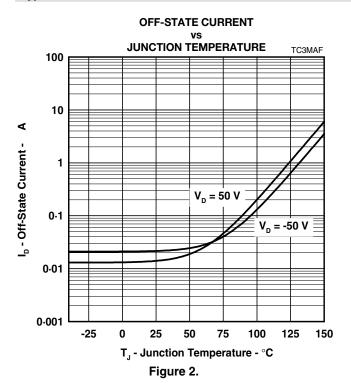
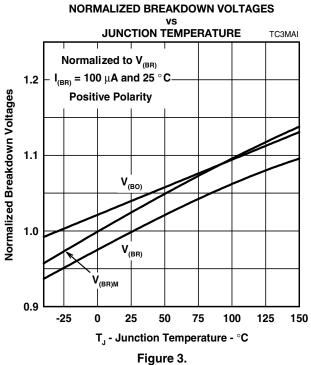


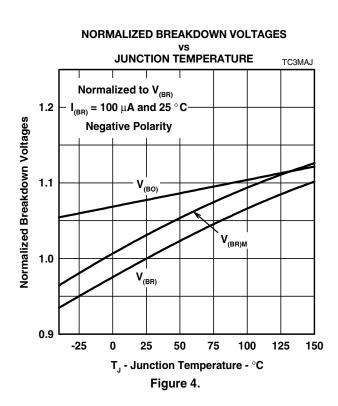
Figure 1. Voltage-Current Characteristics for any Terminal Pair

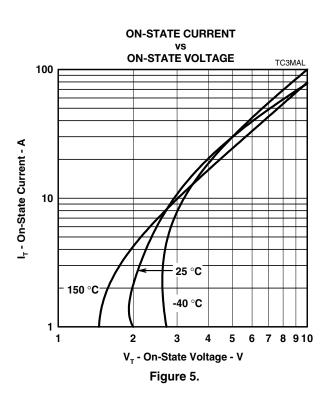
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#### Typical Characteristics - R and G or T and G Terminals



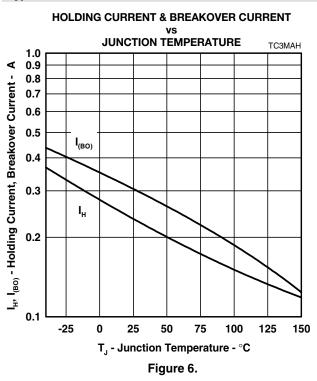


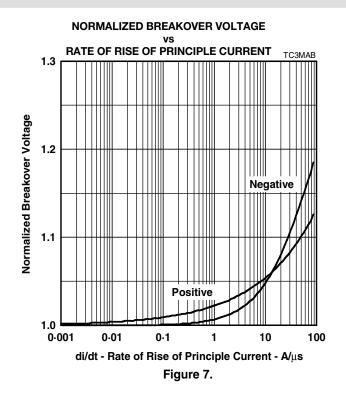


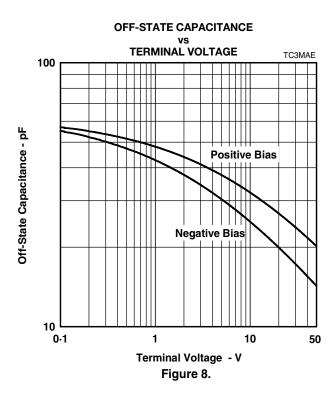


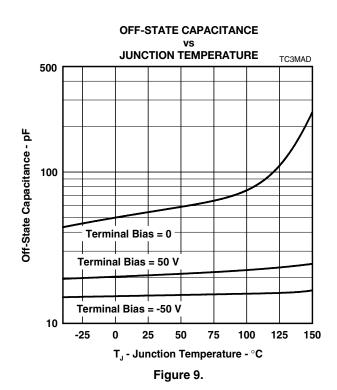
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#### Typical Characteristics - R and G or T and G Terminals

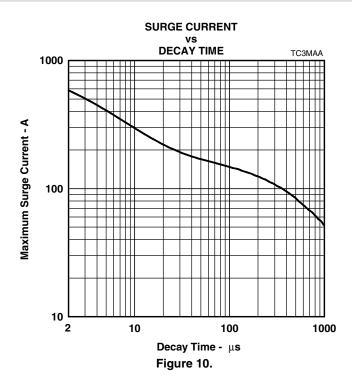






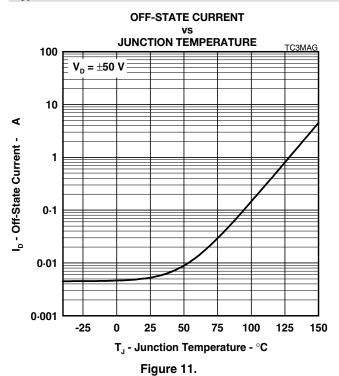


### Typical Characteristics - R and G or T and G Terminals



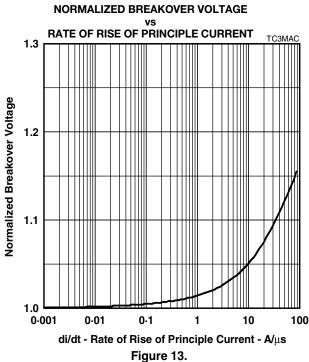
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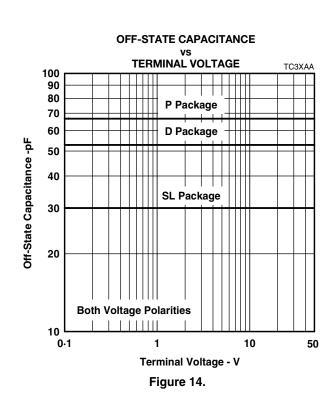
#### Typical Characteristics - R and T Terminals



## **NORMALIZED BREAKDOWN VOLTAGES** JUNCTION TEMPERATURE ТСЗМАК Normalized to $V_{\rm (BR)}$ $I_{(BR)} = 100 \,\mu\text{A} \text{ and } 25 \,^{\circ}\text{C}$ 1.2 Normalized Breakdown Voltages **Both Polarities** 1.1 1.0 $\mathbf{V}_{(\mathrm{BR})}$ 0.9 -25 0 25 50 75 100 125 150 T, - Junction Temperature - °C

Figure 12.

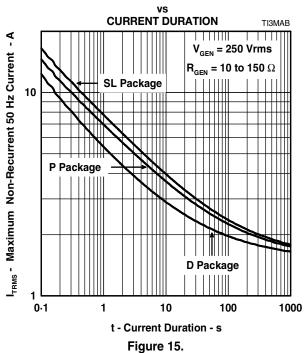


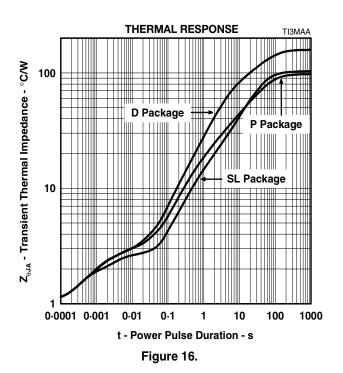


# BOURNS

#### **Thermal Information**

#### MAXIMUM NON-RECURRING 50 Hz CURRENT







#### APPLICATIONS INFORMATION

#### **Electrical Characteristics**

The electrical characteristics of a TISP® device are strongly dependent on junction temperature,  $T_J$ . Hence, a characteristic value will depend on the junction temperature at the instant of measurement. The values given in this data sheet were measured on commercial testers, which generally minimize the temperature rise caused by testing. Application values may be calculated from the parameters' temperature coefficient, the power dissipated and the thermal response curve,  $Z_\theta$  (see M. J. Maytum, "Transient Suppressor Dynamic Parameters." TI Technical Journal, vol. 6, No. 4, pp.63-70, July-August 1989).

#### **Lightning Surge**

#### **Wave Shape Notation**

Most lightning tests, used for equipment verification, specify a unidirectional sawtooth waveform which has an exponential rise and an exponential decay. Wave shapes are classified in terms of peak amplitude (voltage or current), rise time and a decay time to 50% of the maximum amplitude. The notation used for the wave shape is *amplitude*, *rise time/decay time*. A 50 A, 5/310  $\mu$ s wave shape would have a peak current value of 50 A, a rise time of 5  $\mu$ s and a decay time of 310  $\mu$ s. The TISP® surge current graph comprehends the wave shapes of commonly used surges.

#### Generators

There are three categories of surge generator type, single wave shape, combination wave shape and circuit defined. Single wave shape generators have essentially the same wave shape for the open circuit voltage and short circuit current (e.g.  $10/1000~\mu s$  open circuit voltage and short circuit current). Combination generators have two wave shapes, one for the open circuit voltage and the other for the short circuit current (e.g.  $1.2/50~\mu s$  open circuit voltage and  $8/20~\mu s$  short circuit current). Circuit specified generators usually equate to a combination generator, although typically only the open circuit voltage waveshape is referenced (e.g.  $a~10/700~\mu s$  open circuit voltage generator typically produces a  $5/310~\mu s$  short circuit current). If the combination or circuit defined generators operate into a finite resistance, the wave shape produced is intermediate between the open circuit and short circuit values.

#### **Current Rating**

When the TISP® device switches into the on-state it has a very low impedance. As a result, although the surge wave shape may be defined in terms of open circuit voltage, it is the current wave shape that must be used to assess the required TISP® surge capability. As an example, the ITU-T K.21 1.5 kV,  $10/700 \,\mu s$  open circuit voltage surge is changed to a 38 A,  $5/310 \,\mu s$  current waveshape when driving into a short circuit. Thus, the TISP® surge current capability, when directly connected to the generator, will be found for the ITU-T K.21 waveform at 310  $\mu s$  on the surge graph and not 700  $\mu s$ . Some common short circuit equivalents are tabulated below:

Standard	Open Circuit Voltage	Short Circuit Current
ITU-T K.21	1.5 kV, 10/700 μs	37.5 A, 5/310 μs
ITU-T K.20	1 kV, 10/700 μs	25 A, 5/310 μs
IEC 61000-4-5, combination wave generator	1.0 kV, 1.2/50 μs	500 A, 8/20 μs
Telcordia GR-1089-CORE	1.0 kV, 10/1000 μs	100 A, 10/1000 μs
Telcordia GR-1089-CORE	2.5 kV, 2/10 μs	500 A, 2/10 μs
FCC Part 68, Type A	1.5 kV, <10/>160 μs	200 A,<10/>160 μs
FCC Part 68, Type A	800 V, <10/>560 μs	100 A,<10/>160 μs
FCC Part 68, Type B	1.5 kV, 9/720 μs	37.5 A, 5/320 μs

Any series resistance in the protected equipment will reduce the peak circuit current to less than the generators' short circuit value. A 1 kV open circuit voltage, 100 A short circuit current generator has an effective output impedance of 10  $\Omega$  (1000/100). If the equipment has a series resistance of 25  $\Omega$ , then the surge current requirement of the TISP® device becomes 29 A (1000/35) and not 100 A.



#### **APPLICATIONS INFORMATION**

#### **Protection Voltage**

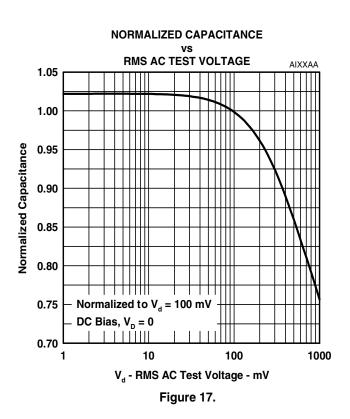
The protection voltage,  $(V_{(BO)})$ , increases under lightning surge conditions due to thyristor regeneration. This increase is dependent on the rate of current rise, di/dt, when the TISP® device is clamping the voltage in its breakdown region. The  $V_{(BO)}$  value under surge conditions can be estimated by multiplying the 50 Hz rate  $V_{(BO)}$  (250 V/ms) value by the normalized increase at the surge's di/dt (Figure 7). An estimate of the di/dt can be made from the surge generator voltage rate of rise, dv/dt, and the circuit resistance.

As an example, the ITU-T K.21 1.5 kV,  $10/700~\mu s$  surge has an average dv/dt of 150 V/ $\mu s$ , but, as the rise is exponential, the initial dv/dt is higher, being in the region of 450 V/ $\mu s$ . The instantaneous generator output resistance is 25  $\Omega$ . If the equipment has an additional series resistance of 20  $\Omega$ , the total series resistance becomes 45  $\Omega$ . The maximum di/dt then can be estimated as 450/45 = 10 A/ $\mu s$ . In practice, the measured di/dt and protection voltage increase will be lower due to inductive effects and the finite slope resistance of the TISP® breakdown region.

#### Capacitance

#### **Off-state Capacitance**

The off-state capacitance of a TISP® device is sensitive to junction temperature,  $T_J$ , and the bias voltage, comprising of the d.c. voltage,  $V_D$ , and the a.c. voltage,  $V_d$ . All the capacitance values in this data sheet are measured with an a.c. voltage of 100 mV. The typical 25 °C variation of capacitance value with a.c. bias is shown in Figure 17. When  $V_D >> V_d$ , the capacitance value is independent on the value of  $V_d$ . The capacitance is essentially constant over the range of normal telecommunication frequencies.



#### **APPLICATIONS INFORMATION**

#### **Longitudinal Balance**

Figure 18 shows a three terminal TISP® device with its equivalent "delta" capacitance. Each capacitance,  $C_{TG}$ ,  $C_{RG}$  and  $C_{TR}$ , is the true terminal pair capacitance measured with a three terminal or guarded capacitance bridge. If wire R is biased at a larger potential than wire T, then  $C_{TG}$ > $C_{RG}$ . Capacitance  $C_{TG}$  is equivalent to a capacitance of  $C_{RG}$  in parallel with the capacitive difference of  $(C_{TG} - C_{RG})$ . The line capacitive unbalance is due to  $(C_{TG} - C_{RG})$  and the capacitance shunting the line is  $C_{TR} + C_{RG}/2$ .

All capacitance measurements in this data sheet are three terminal guarded to allow the designer to accurately assess capacitive unbalance effects. Simple two terminal capacitance meters (unguarded third terminal) give false readings as the shunt capacitance via the third terminal is included.

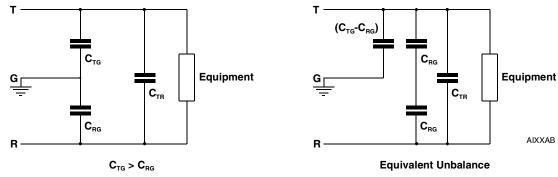
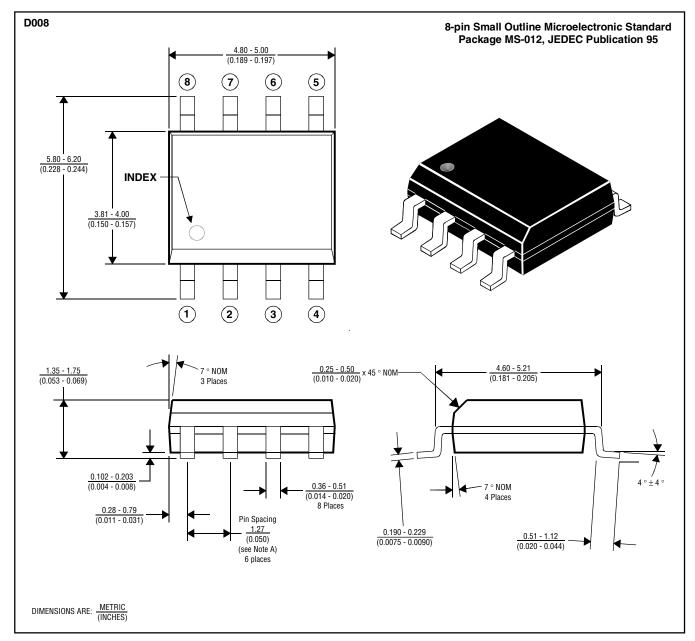


Figure 18.

#### **MECHANICAL DATA**

#### **D008 Plastic Small-outline Package**

This small-outline package consists of a circuit mounted on a lead frame and encapsulated within a plastic compound. The compound will withstand soldering temperature with no deformation, and circuit performance characteristics will remain stable when operated in high humidity conditions. Leads require no additional cleaning or processing when used in soldered assembly.



MDXXAAC

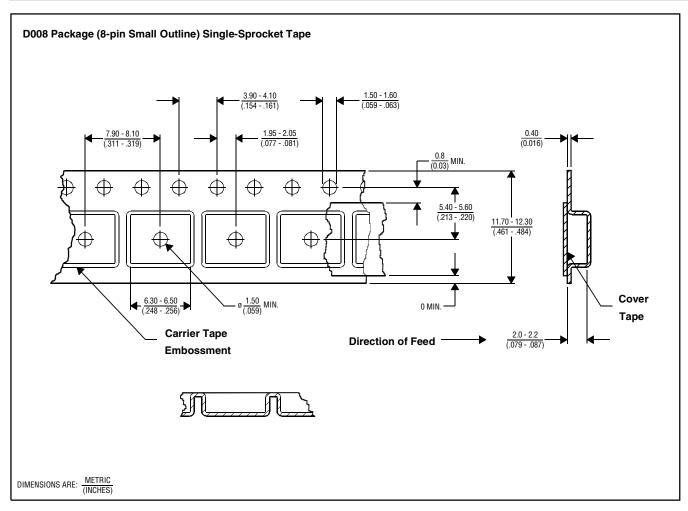
NOTES: A. Leads are within 0.25 (0.010) radius of true position at maximum material condition.

- B. Body dimensions do not include mold flash or protrusion.
- C. Mold flash or protrusion shall not exceed 0.15 (0.006).
- D. Lead tips to be planar within  $\pm 0.051$  (0.002).

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#### **MECHANICAL DATA**

#### **D008 Tape Dimensions**



NOTES: A. Taped devices are supplied on a reel of the following dimensions:-

**MDXXATB** 

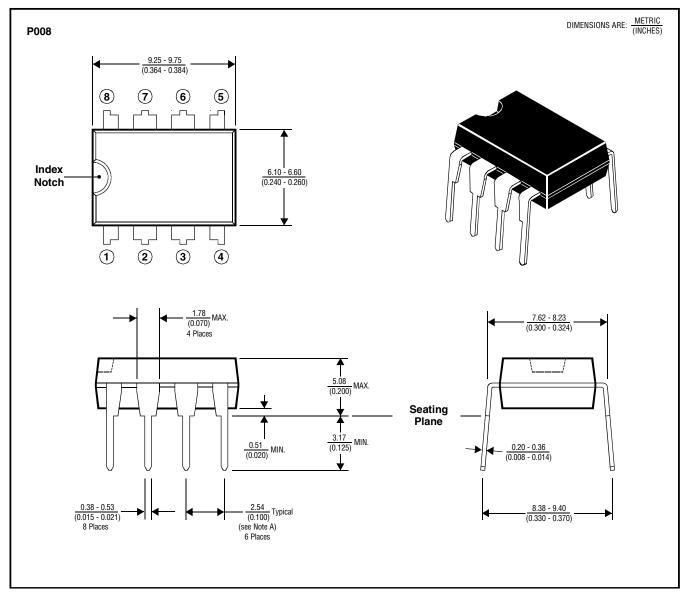
 $\begin{array}{lll} \mbox{Reel diameter:} & \frac{330 + 0.0/ - 4.0}{(12.992 + 0.0/ - 157)} \\ \mbox{Reel hub diameter:} & \frac{100 \pm 2.0}{(3.937 \pm .079)} \\ \mbox{Reel axial hole:} & \frac{13.0 \pm 0.2}{(.512 \pm .008)} \\ \end{array}$ 

B. 2500 devices are on a reel.

#### **MECHANICAL DATA**

#### **D008 Plastic Dual-in-Line Package**

This dual-in-line package consists of a circuit mounted on a lead frame and encapsulated within a plastic compound. The compound will withstand soldering temperature with no deformation, and circuit performance characteristics will remain stable when operated in high humidity conditions. The package is intended for insertion in mounting-hole rows on 7.62 (0.300) centers. Once the leads are compressed and inserted, sufficient tension is provided to secure the package in the board during soldering. Leads require no additional cleaning or processing when used in soldered assembly.



MDXXCF

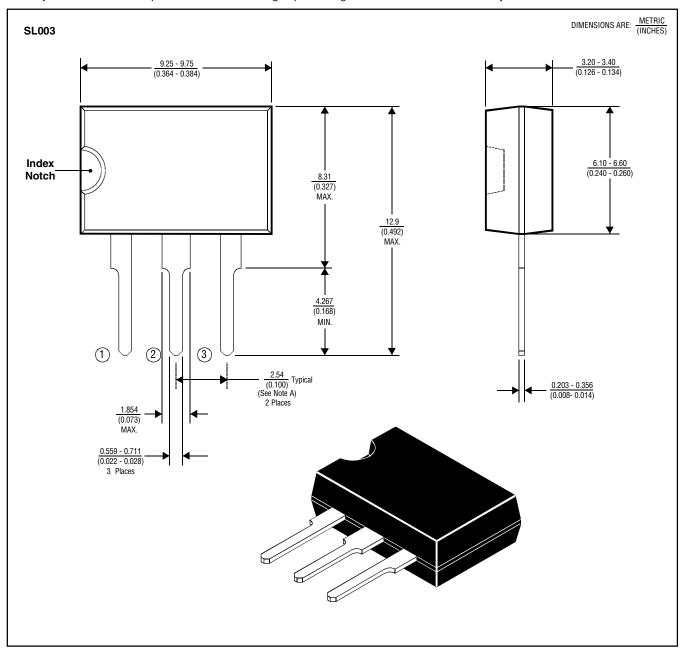
NOTES: A. Each pin centerline is located within 0.25 (0.010) of its true longitudinal position.

B. Dimensions fall within JEDEC MS001 - R-PDIP-T, 0.300" Dual-In-Line Plastic Family.

#### **MECHANICAL DATA**

## SL003 3-pin Plastic Single-In-Line Package

This single-in-line package consists of a circuit mounted on a lead frame and encapsulated within a plastic compound. The compound will withstand soldering temperature with no deformation, and circuit performance characteristics will remain stable when operated in high humidity conditions. Leads require no additional cleaning or processing when used in soldered assembly.



MDXXCE

NOTES: A. Each pin centerline is located within 0.25 (0.010) of its true longitudinal position.

B. Body molding flash of up to 0.15 (0.006) may occur in the package lead plane.

# AMEYA360 Components Supply Platform

## **Authorized Distribution Brand:**

























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